## **SKNH 91**



## SEMIPACK® 1

# Modules with Thyristor and Free-Wheeling Diode

#### **SKNH 91**

#### **Features**

- Heat transfer through ceramic isolated metal baseplate
- Hard soldered joints for high reliability
- UL recognized, file no. E 63 532
- Electrical data see also data sheet SKKH 92

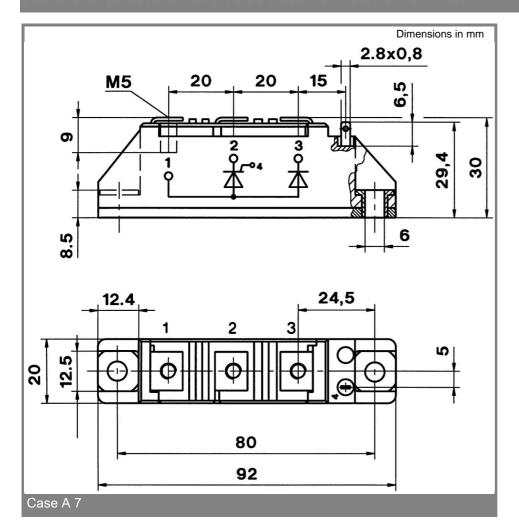
### **Typical Applications**

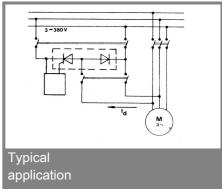
- Special modules for DC braking of AC induction motor
- 1) available on request

$V_{RSM}$	$V_{RRM}, V_{DRM}$	I <sub>TRMS</sub> = 150 A (maximum value for continuous operation)		
V	V	I <sub>TAV</sub> = 95 A (sin. 180; T <sub>c</sub> = 85 °C)		
1300	1200	SKNH 91/12E		
1500	1400	SKNH 91/14E		
1700	1600	SKNH 91/16E		
1900	1800	SKNH 91/18E <sup>1)</sup>		

Symbol	Conditions	Values	Units
$I_{TAV}$	sin. 180; T <sub>c</sub> = 85 (100) °C;	95 (68 )	Α
I <sub>TSM</sub>	T <sub>vi</sub> = 25 °C; 10 ms	2000	Α
	T <sub>vi</sub> = 125 °C; 10 ms	1750	Α
i²t	T <sub>vj</sub> = 25 °C; 8,3 10 ms	20000	A²s
	T <sub>vj</sub> = 125 °C; 8,3 10 ms	15000	A²s
V <sub>T</sub>	T <sub>vi</sub> = 25 °C; I <sub>T</sub> = 300 A	max. 1,65	V
$V_{T(TO)}$	T <sub>vi</sub> = 125 °C	max. 0,9	V
r <sub>T</sub>	T <sub>vj</sub> = 125 °C	max. 2	mΩ
$I_{DD}$ ; $I_{RD}$	$T_{vj}$ = 125 °C; $V_{RD} = V_{RRM}$ ; $V_{DD} = V_{DRM}$	max. 20	mA
t <sub>gd</sub>	$T_{vj} = 25  ^{\circ}\text{C}; I_{G} = 1  \text{A}; di_{G}/dt = 1  \text{A/}\mu\text{s}$	1	μs
t <sub>gr</sub>	$V_{\rm D} = 0.67 * V_{\rm DRM}$	2	μs
(di/dt) <sub>cr</sub>	T <sub>vj</sub> = 125 °C	max. 150	A/µs
(dv/dt) <sub>cr</sub>	T <sub>vj</sub> = 125 °C	max. 1000	V/µs
t <sub>q</sub>	$T_{vi} = 125 ^{\circ}\text{C}$ ,	100	μs
I <sub>H</sub>	$T_{vj} = 25 ^{\circ}\text{C}$ ; typ. / max.	/ 250	mA
IL	$T_{vj} = 25 ^{\circ}\text{C};  R_{G} = 33 \Omega;  \text{typ. / max.}$	/ 600	mA
V <sub>GT</sub>	T <sub>vj</sub> = 25 °C; d.c.	min. 3	V
I <sub>GT</sub>	$T_{vj} = 25  ^{\circ}\text{C}; \text{d.c.}$	min. 150	mA
$V_{GD}$	$T_{vj} = 125 ^{\circ}\text{C}; \text{d.c.}$	max. 0,25	V
$I_{GD}$	$T_{vj}$ = 125 °C; d.c.	max. 6	mA
R <sub>th(j-c)</sub>	cont.; per thyristor / per module	0,28 / 0,14	K/W
$R_{th(j-c)}$	sin. 180; per thyristor / per module	0,3 / 0,15	K/W
R <sub>th(j-c)</sub>	rec. 120; per thyristor / per module	0,32 / 0,16	K/W
R <sub>th(c-s)</sub>	per thyristor / per module	0,2 / 0,1	K/W
$T_{vj}$		- 40 <b>+</b> 125	°C
$T_{stg}$		- 40 <b>+</b> 125	°C
V <sub>isol</sub>	a. c. 50 Hz; r.m.s.; 1 s / 1 min.	3600 / 3000	V~
M <sub>s</sub>	to heatsink	5 ± 15 %	Nm
M <sub>t</sub>	to terminals	5 ± 15 %	Nm
а		5 * 9,81	m/s²
m	approx.	120	g
Case		A 7	







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